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N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω) TYP.	I _D (A)	Q _g (TYP.)			
100	0.0032 at V _{GS} = 10 V	166	105 nC			

TO-220AB G D S Top View N-Channel MOSFET

FEATURES

- Super Trench III
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested



APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management

ABSOLUTE MAXIMUM RATINGS	$I_C = 25$ C, unless other	rwise noted)			
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V _{GS}	± 20	7 V	
Continuous Drain Current (T. – 150 °C)	T _C = 25 °C		166		
Continuous Drain Current (T _J = 150 °C)	T _C = 100 °C	I _D	115		
Pulsed Drain Current (t = 100 μs)		I _{DM}	610	A	
Avalanche Current	L = 0.1 mH	I _{AS}	50		
Single Avalanche Energy ^a	L = U.1 IIIII	E _{AS}	952	mJ	
Maximum Dawar Dissination 3	T _C = 25 °C	В	260 ^b	W	
Maximum Power Dissipation ^a	T _C = 125 °C	P _D	115 ^b	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	35	°C ///		
Junction-to-Case (Drain)	R _{thJC}	0.71	°C/W		

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



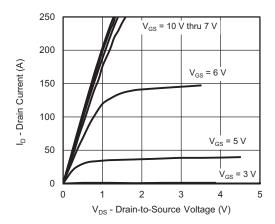
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	- V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_D=250\;\mu A$	2 3.0 4		V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$	-	-	± 100	nA
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 100 V, V_{GS} = 0 V, T_J = 125 °C	-	-	100	
		V_{DS} = 100 V, V_{GS} = 0 V, T_J = 175 °C	-	-	2	mA
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	166	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 65 \text{ A}$	-	0.0032	0.0038	Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 65 A	-	90	-	S
Dynamic ^b						
Input Capacitance	C _{iss}		-	6520	-	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	-	625	-	
Reverse Transfer Capacitance	C _{rss}		-	32	-	
Total Gate Charge ^c	Qg		-	105	-	nC
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 65 \text{ A}$	-	38	-	
Gate-Drain Charge ^c	Q_{gd}		-	26	-	
Gate Resistance	R_g	f = 1 MHz	-	1.5	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	20	-	
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, R_{L} = 1.67 \Omega$	-	11.5	-	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 65 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	48	=	ns
Fall Time ^c	t _f		-	9	-	
Drain-Source Body Diode Ratings ar	nd Characteri	stics ^b (T _C = 25 °C)				
Pulsed Current (t = 100 μs)	I _{SM}		-	-	610	Α
Forward Voltage ^a	V_{SD}	I _F = 65 A, V _{GS} = 0 V	-	-	1.2	V
Reverse Recovery Time	t _{rr}		-	78	-	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 65 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	5	-	Α
Reverse Recovery Charge	Q _{rr}		-	150	-	nC

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

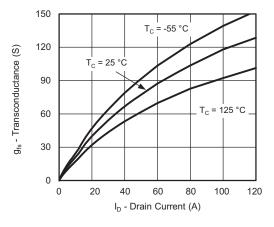
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



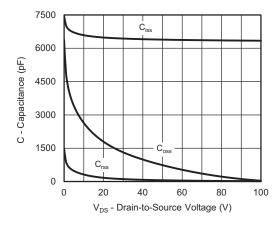
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



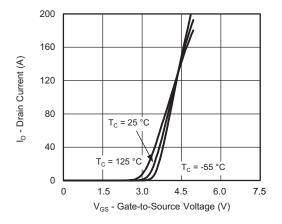
Output Characteristics



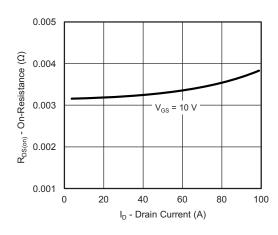
Transconductance



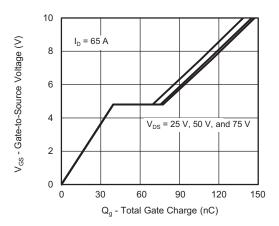
Capacitance



Transfer Characteristics



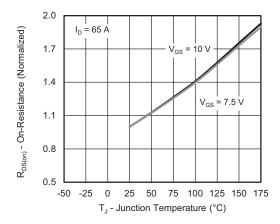
On-Resistance vs. Drain Current



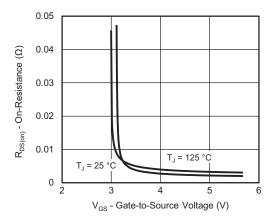
Gate Charge



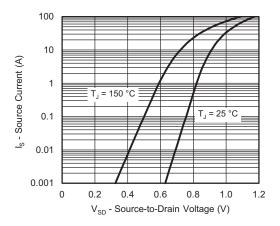
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



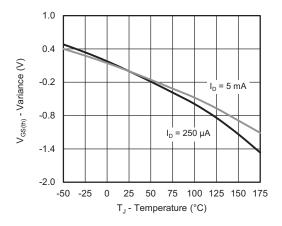
On-Resistance vs. Junction Temperature



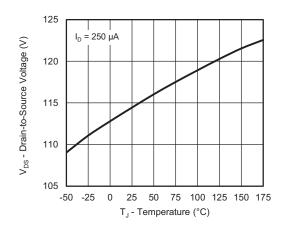
On-Resistance vs. Gate-to-Source Voltage



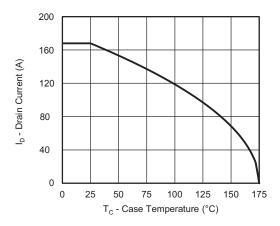
Source Drain Diode Forward Voltage



Threshold Voltage



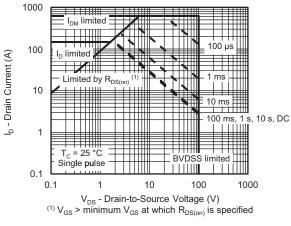
Drain Source Breakdown vs. Junction Temperature

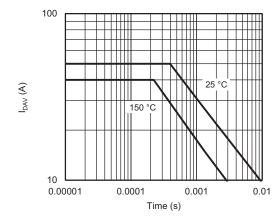


Current De-Rating



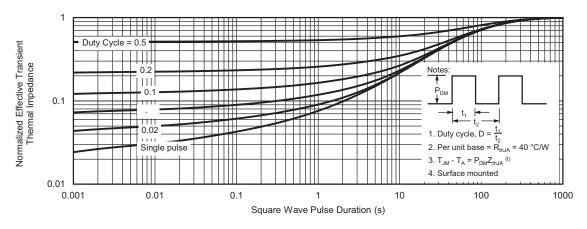
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)





Safe Operating Area

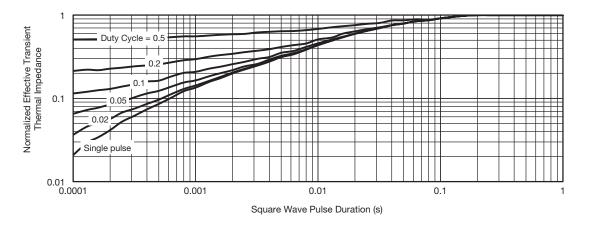
 I_{DAV} vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

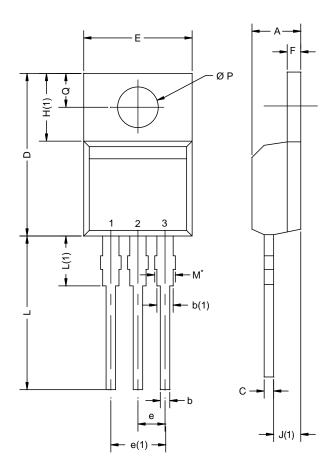
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



TO-220AB



	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
Е	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØΡ	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471					

Notes

 $^{^{*}}$ M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM





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